

1. A semiconductor device with a plurality of semiconductor chips stacked on a substrate, wherein said semiconductor device comprising;

a witing layer disposed so as to be sandwiched between said semiconductor chips, and

a plurality of bonding pads, for connecting a bonding wire, provided on said wiring layer, thereto.

- 2. A semiconductor device according to claim 1, wherein a connection wiring for connecting among said bonding pads is provided in said wiring layer.
- 3. A semiconductor device according to claim 1, wherein said plurality of bonding pads are disposed so as to surround a semiconductor chip stacked on an upper surface of said wiring layer.
- 4. A semiconductor device according to claim 1, wherein a via hole is provided in said wiring layer, said via hole is connected to a bonding pad of a semiconductor chip disposed below said wiring layer.
- 5. A semiconductor device with a plurality of semiconductor chips stacked on a substrate, wherein said semiconductor device comprising;

a wiring layer disposed so as to be sandwiched between said semiconductor chips,

a plurality of bonding pads, for connecting a bonding wire, provided on said wiring layer, thereto and

a connection wiring for connecting said bonding pads provided in said wiring layer.

6. A semiconductor device with \a plurality of

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semiconductor chips stacked on a substrate, wherein said semiconductor device comprising;

- a wiring layer disposed so as to be sandwiched between said semiconductor chips,
- a plurality of bonding pads, for connecting a bonding wire, provided on said wiring layer, thereto,
- a connection wiring for connecting among said bonding pads provided in said wiring layer, and
- a via hole, connected to said bonding pad of a semiconductor chip disposed below said wiring layer, and provided on said wiring layer.

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